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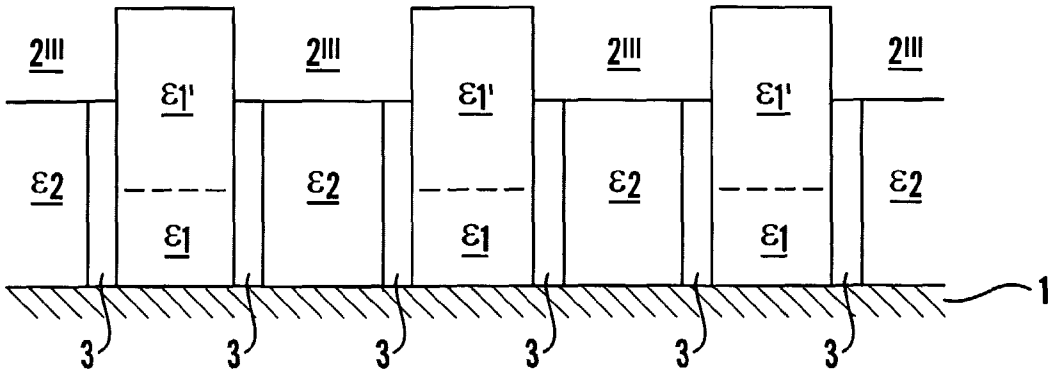
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(54) Title: A METHOD FOR FABRICATING HIGH ASPECT RATIO ELECTRODES



(57) Abstract: In a method for building high aspect ratio electrodes in an electrode means (*E*) comprising parallel electrodes (ε_1, ε_2) in a dense arrangement, the electrodes are built in a repeatedly performed sequence of successive process steps involving the use of only one and the same photomask in every patterning step, the electrodes being formed with a desired aspect ratio according to the number of times the sequence is repeated, and top surface of the electrode means planarized in a final process step.

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